

## PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Shipping†
FDD86367	FDD86367	DPAK3 (TO-252 3 LD) (Pb-Free)	13"	16 mm	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

$B_{V_{DS}}$	Drain-to-Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$	80	–	–	V
$I_{DSS}$	Drain-to-Source Leakage Current	$V_{DS} = 80\ \text{V}$ , $V_{GS} = 0\ \text{V}$	$T_J = 25^\circ\text{C}$	–	–	1 mA
			$T_J = 175^\circ\text{C}$ (Note 4)	–	–	1 mA
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{GS} = \pm 20\ \text{V}$	–	–	$\pm 100$	nA

## ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\ \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Drain to Source On Resistance	$I_D = 80\ \text{A}$ , $V_{GS} = 10\ \text{V}$	$T_J = 25^\circ\text{C}$	–	3.3	4.2 m $\Omega$
			$T_J = 175^\circ\text{C}$ (Note 4)	–	6.6	8.4 m $\Omega$

## DYNAMIC CHARACTERISTICS

$C_{iss}$	Input Capacitance	$V_{DS} = 40\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	–	4840	–	pF
$C_{oss}$	Output Capacitance		–	814	–	pF
$C_{rss}$	Reverse Transfer Capacitance		–	31	–	pF
$R_g$	Gate Resistance	$V_{GS} = 0.5\ \text{V}$ , $f = 1\ \text{MHz}$	–	2.3	–	$\Omega$
$Q_{g(ToT)}$	Total Gate Charge	$V_{GS} = 0$ to $10\ \text{V}$	$V_{DD} = 40\ \text{V}$ , $I_D = 80\ \text{A}$	–	68	88 nC
$Q_{g(th)}$	Threshold Gate Charge	$V_{GS} = 0$ to $2\ \text{V}$		–	8.8	– nC
$Q_{gs}$	Gate-to-Source Gate Charge	$V_{DD} = 40\ \text{V}$ , $I_D = 80\ \text{A}$	–	22	–	nC
$Q_{gd}$	Gate-to-Drain "Miller" Charge		–	14	–	nC

## SWITCHING CHARACTERISTICS

$t_{on}$	Turn-On Time	$V_{DD} = 40\ \text{V}$ , $I_D = 80\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$	–	–	104	ns
$t_{d(on)}$	Turn-On Delay		–	20	–	ns
$t_r$	Rise Time		–	49	–	ns
$t_{d(off)}$	Turn-Off Delay		–	36	–	ns
$t_f$	Fall Time		–	16	–	ns
$t_{off}$	Turn-Off Time		–	–	80	ns

## DRAIN-SOURCE DIODE CHARACTERISTICS

$V_{SD}$	Source-to-Drain Diode Voltage	$I_{SD} = 80\ \text{A}$ , $V_{GS} = 0\ \text{V}$	–	–	1.3	V
		$I_{SD} = 40\ \text{A}$ , $V_{GS} = 0\ \text{V}$	–	–	1.2	V
$t_{rr}$	Reverse-Recovery Time	$V_{DD} = 64\ \text{V}$ , $I_F = 80\ \text{A}$ , $dI_{SD}/dt = 100\ \text{A}/\mu\text{s}$	–	68	102	ns
$Q_{rr}$	Reverse-Recovery Charge		–	66	106	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at  $T_J = 175^\circ\text{C}$ . Product is not tested to this condition in production.

## TYPICAL CHARACTERISTICS

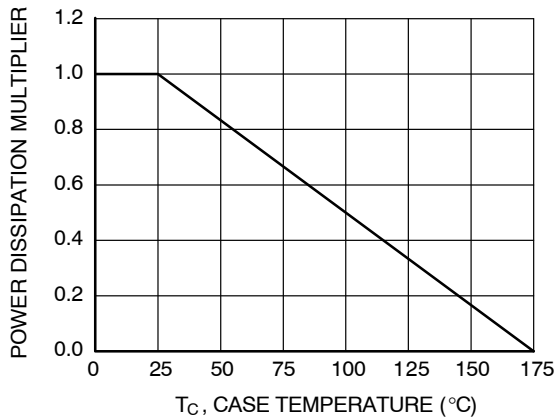


Figure 1. Normalized Power Dissipation vs. Case Temperature

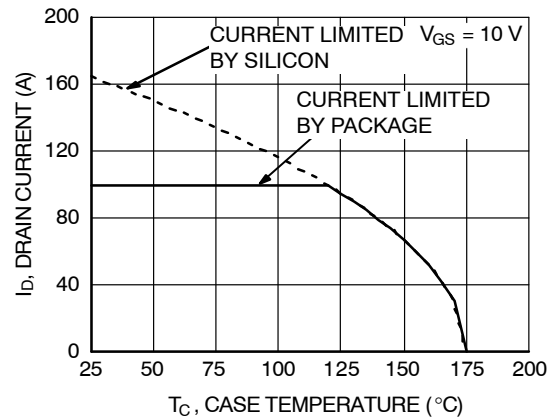


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

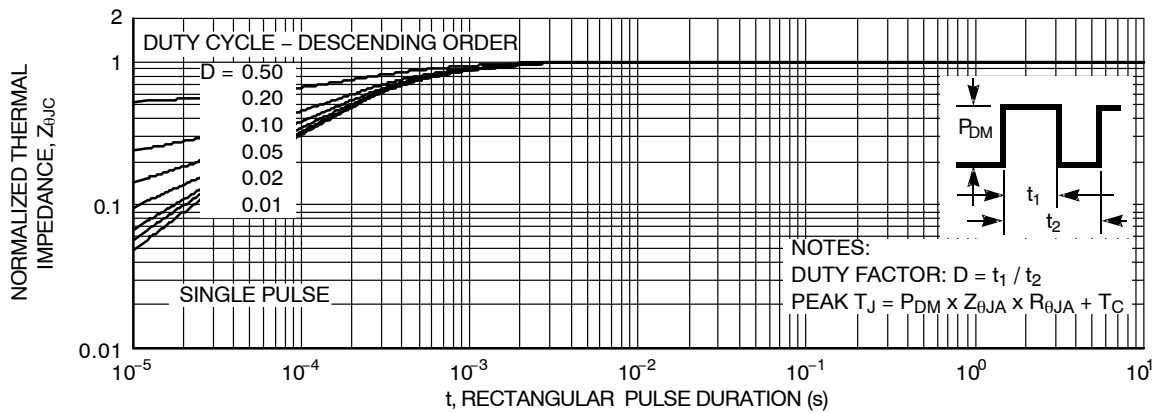


Figure 3. Normalized Maximum Transient Thermal Impedance

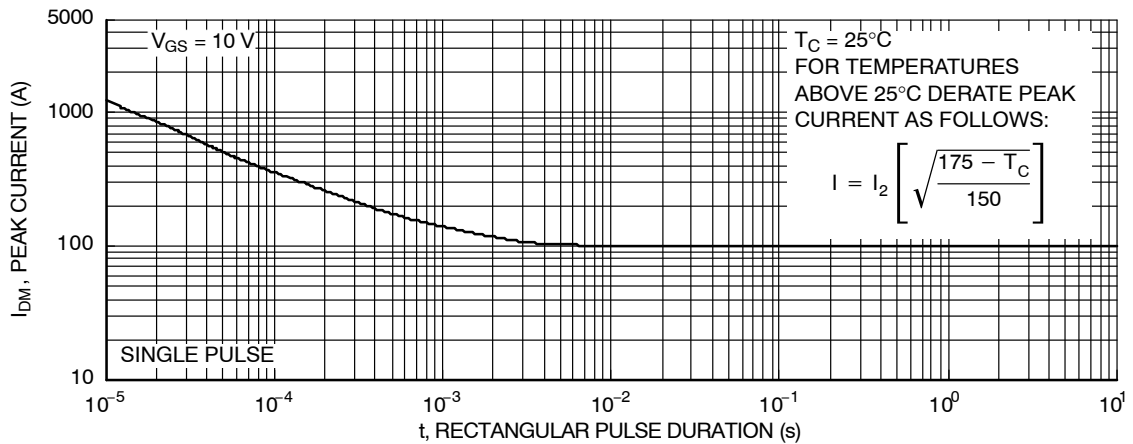


Figure 4. Peak Current Capability

## TYPICAL CHARACTERISTICS (continued)

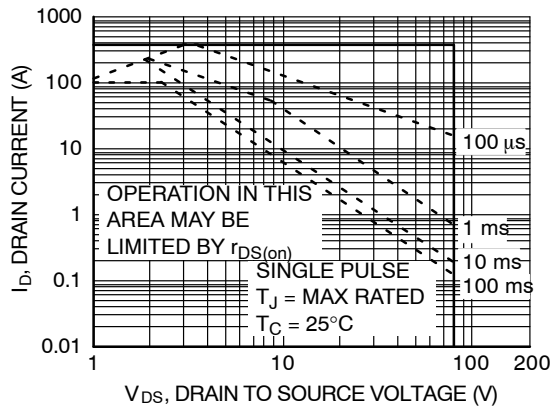


Figure 5. Forward Bias Safe Operating Area

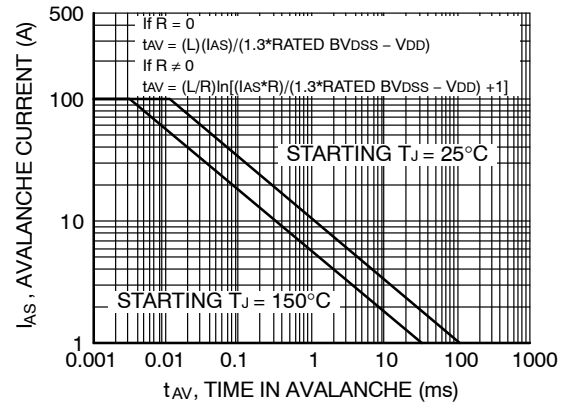
NOTE: Refer to ON Application Notes [AN7514](#) and [AN7515](#)

Figure 6. Unclamped Inductive Switching Capability

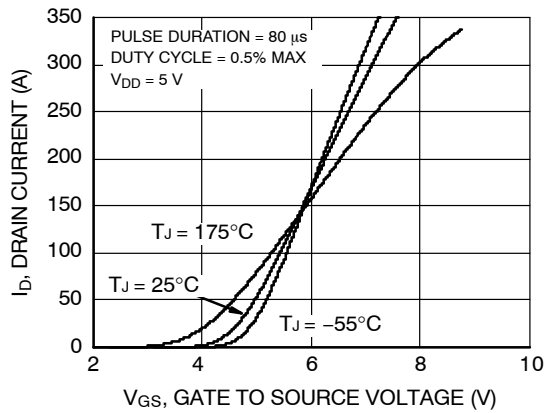


Figure 7. Transfer Characteristics

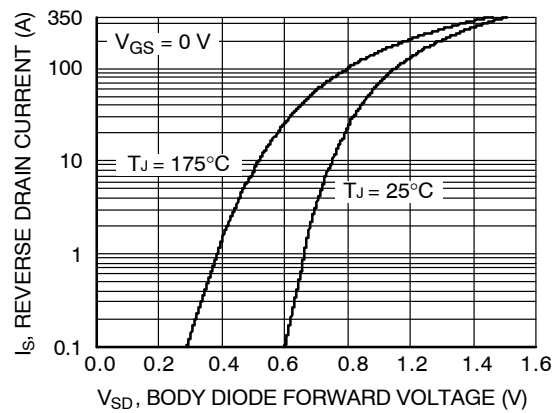


Figure 8. Forward Diode Characteristics

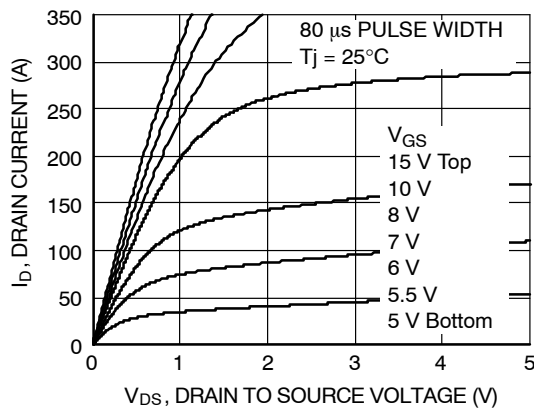


Figure 9. Saturation Characteristics

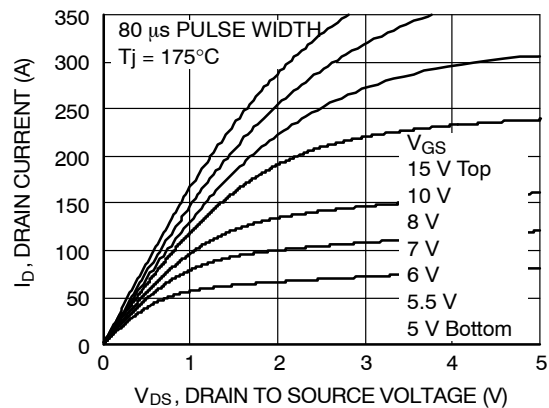


Figure 10. Saturation Characteristics

## TYPICAL CHARACTERISTICS (continued)

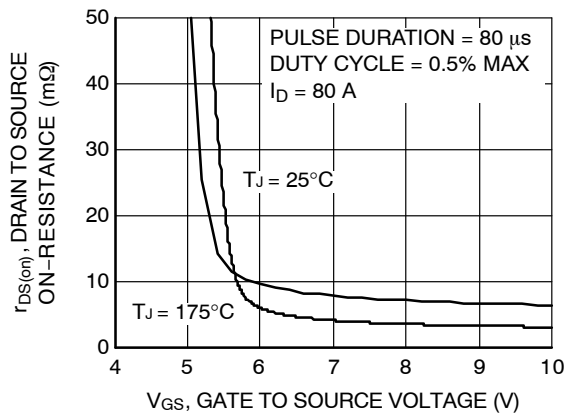
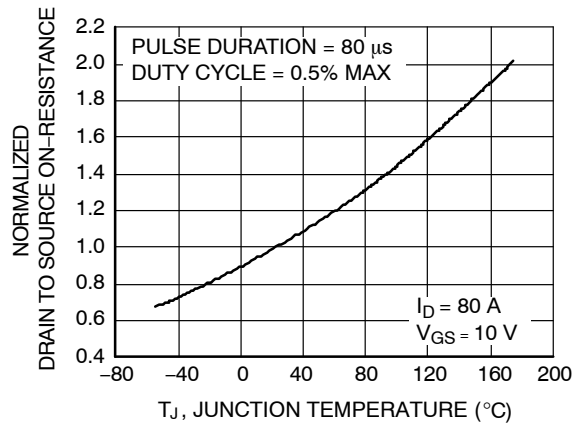
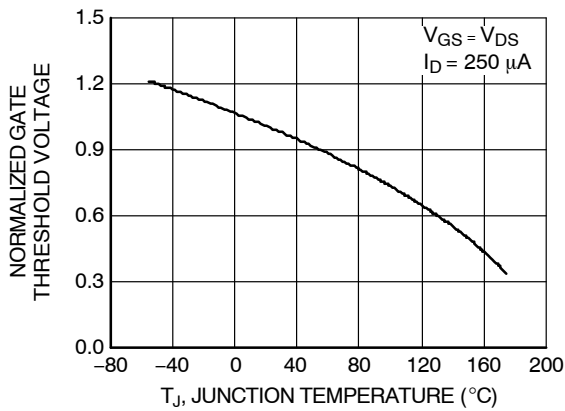
Figure 11.  $R_{DS(on)}$  vs. Gate VoltageFigure 12. Normalized  $R_{DS(on)}$  vs. Junction Temperature

Figure 13. Normalized Gate Threshold Voltage vs. Temperature

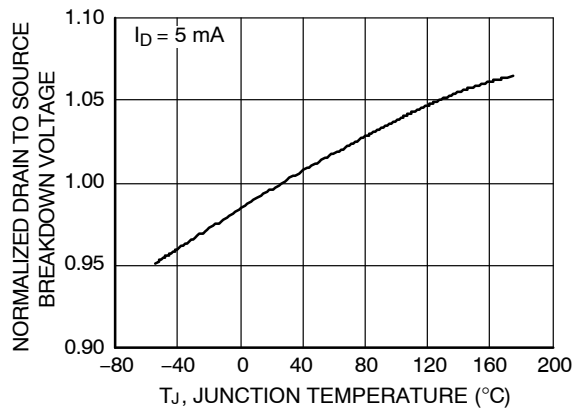


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

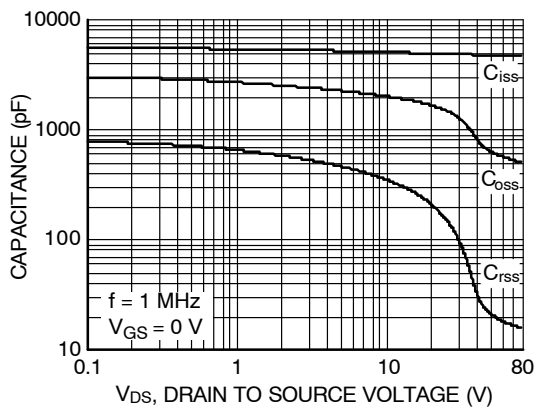


Figure 15. Capacitance vs. Drain to Source Voltage

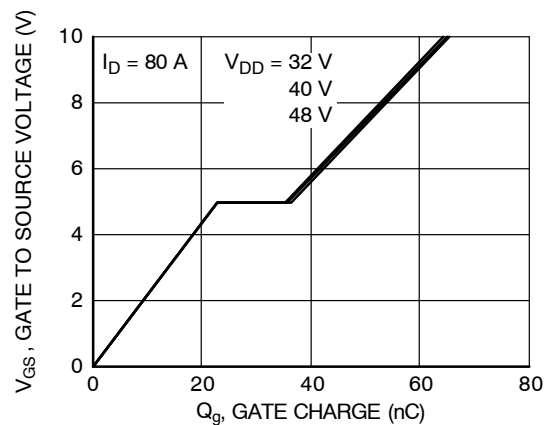
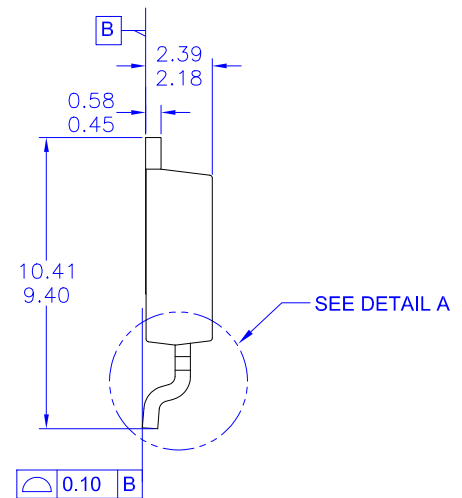
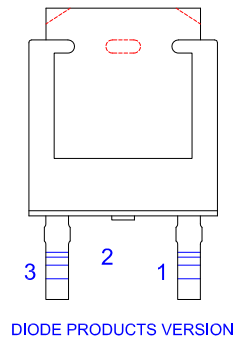
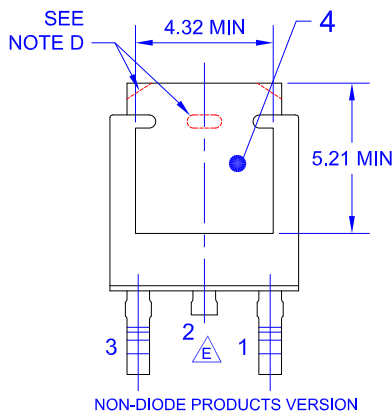
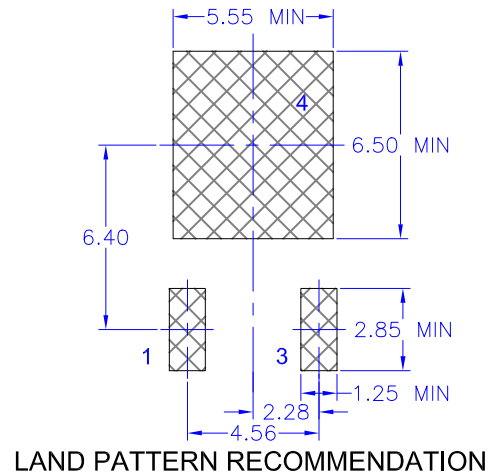
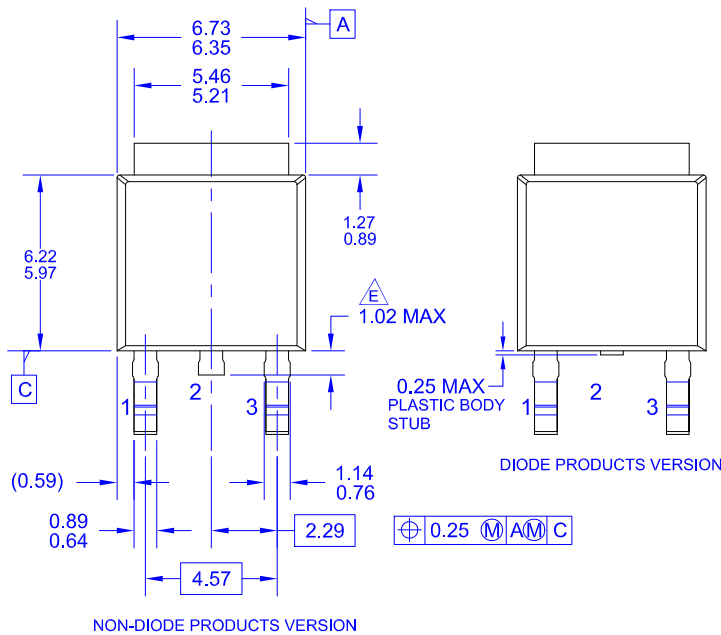


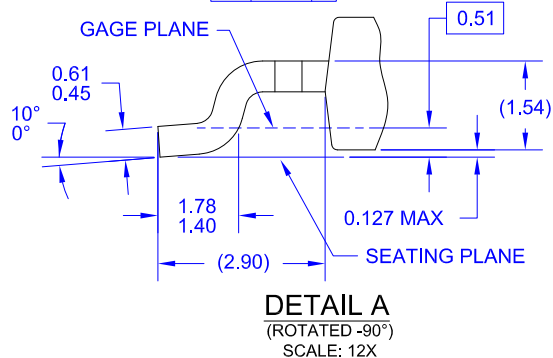
Figure 16. Gate Charge vs. Gate to Source Voltage

### DPAK3 (TO-252 3 LD) CASE 369AS ISSUE O

DATE 30 SEP 2016



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
  - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
  - E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
  - F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



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<b>DESCRIPTION:</b>	<b>DPAK3 (TO-252 3 LD)</b>	<b>PAGE 1 OF 1</b>

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